



Schottky Barrier Diode

Qualified per MIL-PRF-19500/444

Qualified Levels: JAN, JANTX, and JANTXV

DESCRIPTION

This Schottky barrier diode is metallurgically bonded and offers military grade qualifications for high-reliability applications on "1N" prefixed numbers. This small diode is hermetically sealed and bonded into a DO-35 glass package.

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FEATURES

- JEDEC registered 1N5711-1, 1N5712-1, 1N6857-1, and 1N6858-1 numbers.
- Metallurgically bonded.
- JAN, JANTX, JANTXV and commercial qualifications also available per MIL-PRF-19500/444 on "1N" numbers only.

(See Part Nomenclature for all available options).

RoHS compliant versions available (commercial grade only).

APPLICATIONS / BENEFITS

- Low reverse leakage characteristics.
- Small size for high density mounting using flexible thru-hole leads (see package illustration).
- ESD sensitive to Class 1.

DO-213AA package

(surface mount) 1N5711UR-1, 1N5712UR-1, 1N6857UR-1, and 1N6858UR-1

DO-35 (DO-204AH)

Also available in:

📆 UB package

(3-pin surface mount)
1N5711UB, 1N5712UB

Package

(B, CC, CA)

MAXIMUM RATINGS @ 25 °C unless otherwise stated

Parameters/Test Conditions	Symbol	Value	Unit
Junction and Storage Temperature	T_J and T_{STG}	-65 to +150	°C
Thermal Resistance, Junction-to-Lead	$R_{\Theta JL}$	250	°C/W
@ lead length = 0.375 inch (9.52 mm) from body			
Average Rectified Output Current:			
1N5711 ⁽¹⁾	Io	33	mA
DSB2810, DSB5712, 1N5712 & 1N6858 (2)		75	
1N6857 ⁽³⁾		150	
Solder Temperature @ 10 s		260	°C

NOTES: 1. At $T_L = +130$ °C and L = 0.375 inch, derate I_O to 0 at +150°C.

2. At T_L = +110°C and L = 0.375 inch, derate I_O to 0 at +150°C.

3. At $T_L = +70$ °C and L = 0.375 inch, derate I_O to 0 at +150°C.

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MECHANICAL and PACKAGING

- CASE: Hermetically sealed glass package.
- TERMINALS: Tin/lead plated or RoHS compliant matte-tin (on commercial grade only) over copper clad steel. Solderable per MIL-STD-750, method 2026.
- POLARITY: Cathode indicated by band.
- MARKING: Part number.
- TAPE & REEL option: Standard per EIA-296. Consult factory for quantities.
- WEIGHT: Approximately 0.2 grams.
- See Package Dimensions on last page.

PART NOMENCLATURE **JAN** 1N5711 -1 (e3)**Reliability Level** RoHS Compliance JAN = JAN level e3 = RoHS compliant (on JANTX = JANTX level commercial grade only) JANTXV = JANTXV level Blank = non-RoHS compliant CDS (reference JANS)* Blank = Commercial grade Metallurgically Bonded *Available only on 1N5711-1 JEDEC type number (see Electrical Characteristics table) **DSB** 2810 (e3)**Diode Schottky Barrier RoHS Compliance** e3 = RoHS compliant Series number Blank = non-RoHS compliant

SYMBOLS & DEFINITIONS				
Symbol	Definition			
С	Capacitance: The capacitance in pF at a frequency of 1 MHz and specified voltage.			
f	frequency			
I_R	Reverse Current: The dc current flowing from the external circuit into the cathode terminal at the specified voltage V _R .			
Io	Average Rectified Output Current: The Output Current averaged over a full cycle with a 50 Hz or 60 Hz sine-wave input and a 180 degree conduction angle.			
t _{rr}	Reverse Recovery Time: The time interval between the instant the current passes through zero when changing from the forward direction to the reverse direction and a specified decay point after a peak reverse current occurs.			
V _(BR)	Breakdown Voltage: A voltage in the breakdown region.			
V _F	Forward Voltage: A positive dc anode-cathode voltage the device will exhibit at a specified forward current.			
V _R	Reverse Voltage: A positive dc cathode-anode voltage below the breakdown region.			
V _{RWM}	Working Peak Reverse Voltage: The peak voltage excluding all transient voltages (ref JESD282-B). Also sometimes known historically as PIV.			

(see Electrical Characteristics

table)



ELECTRICAL CHARACTERISTICS @ 25 °C unless otherwise noted

TYPE NUMBER	MINIMUM BREAKDOWN VOLTAGE	MAXIMUM FORWARD VOLTAGE	MAXIMUM FORWARD VOLTAGE	WORKING PEAK REVERSE VOLTAGE	MAXIMUM REVERSE LEAKAGE CURRENT		MAXIMUM CAPACITANCE @ V _R = 0 VOLTS f = 1.0 MHz
	V _(BR) @ 10 μA	V _F @ 1 mA	V _F @ I _F	V _{RWM}	I _R (2 V _R	С
	Volts	Volts	V @ mA	V (pk)	nA	Volts	pF
1N5711-1	70	0.41	1.0 @ 15	50	200	50	2.0
1N5712-1	20	0.41	1.0 @ 35	16	150	16	2.0
1N6857-1	20	0.35	0.75 @ 35	16	150	16	4.5
1N6858-1	70	0.36	0.65 @ 15	50	200	50	4.5
DSB2810	20	0.41	1.0 @ 35	16	100	15	2.0
DSB5712	20	0.41	1.0 @ 35	16	150	16	2.0



GRAPHS

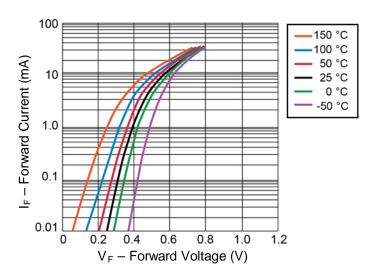


FIGURE 1

<u>I-V Curve showing typical Forward Voltage Variation</u>

Temperature for the 1N5712-1, DSB5712 and DSB2810 Schottky Diodes

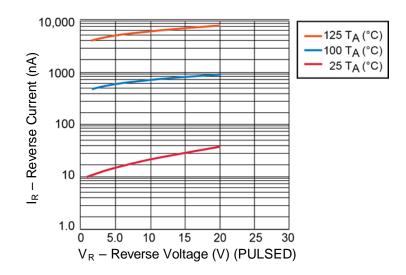


FIGURE 2 1N5712-1, DSB5712 and DSB2810 Typical variation of Reverse Current (I_R) vs Reverse Voltage (V_R) at Various Temperatures



GRAPHS

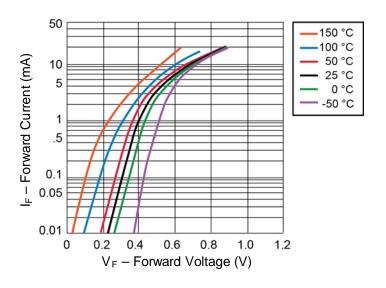


FIGURE 3

I – V curve showing typical Forward Voltage Variation
With Temperature Schottky Diode 1N5711

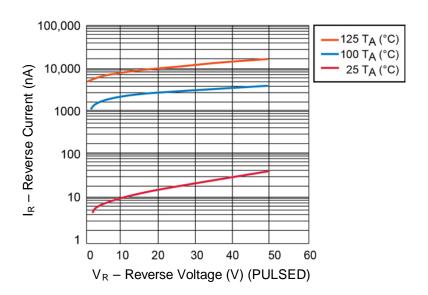


FIGURE 4

1N5711 Typical Variation of Reverse Current (I_R) vs Reverse Voltage (V_R)

at Various Temperatures



GRAPHS

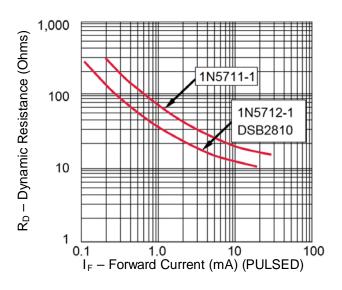
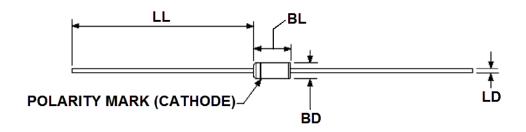


FIGURE 5 Typical Dynamic Resistance (R_D) vs Forward Current (I_F)



PACKAGE DIMENSIONS



NOTES:

- 1. Dimensions are in inches. Millimeters are given for information only.
- 2. Dimensions BL and LD includes all components of the diode periphery expect the section of the leads over which the diameter is controlled.
- 3. Dimension BD shall be measured at the largest diameter.
- 4. In accordance with ASME Y1.4M, diameters are equivalents to φx symbology.

	Dimensions				
Symbol	Inches		Millimeters		Notes
	Min	Max	Min	Max	
BD	0.068	0.076	1.73	1.93	2,3
BL	0.125	0.170	3.18	4.32	2
LD	0.014	0.022	0.36	0.56	
LL	1.000	1.500	25.40	38.10	

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